
HRC0202A

Silicon Schottky Barrier Diode for Rectifying

HITACHI

ADE-208-210D (Z)
Rev 4

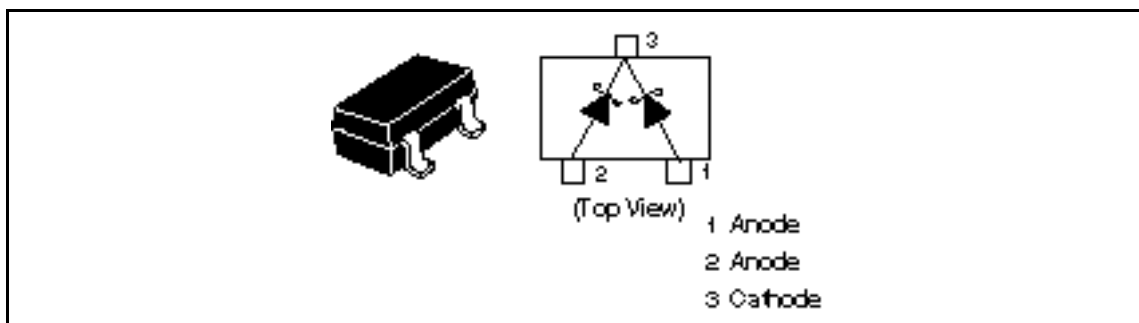
Features

- Σ Low forward voltage drop and suitable for high efficiency rectifying.
- Σ CMPAK Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRC0202A	S16	CMPAK

Outline



HRC0202A

Absolute Maximum Ratings (Ta = 25°C) ^{*1}

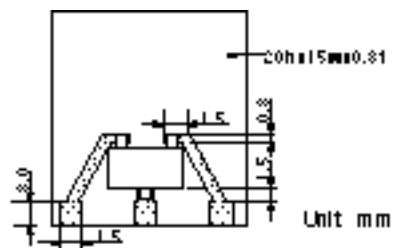
Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}^{*2}	20	V
Average rectified current	I_O^{*2}	200	mA
Non-Repetitive peak forward surge current	I_{FSM}^{*3}	2	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55 to +125	°C

Notes: 1. Two device total
2. See from Fig.4 to Fig.7
3. 10msec sine wave 1 pulse

Electrical Characteristics (Ta = 25°C)^{*1}

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.4	V	$I_F = 100 \text{ mA}$
Reverse current	I_R	—	—	50	μA	$V_R = 20\text{V}$
Thermal resistance	$R_{\text{th(j-a)}}$	—	450	—	$^{\circ}\text{C/W}$	Polyimide board ^{*2}

Notes: 1. Per one device
2. Polyimide board



Main Characteristic

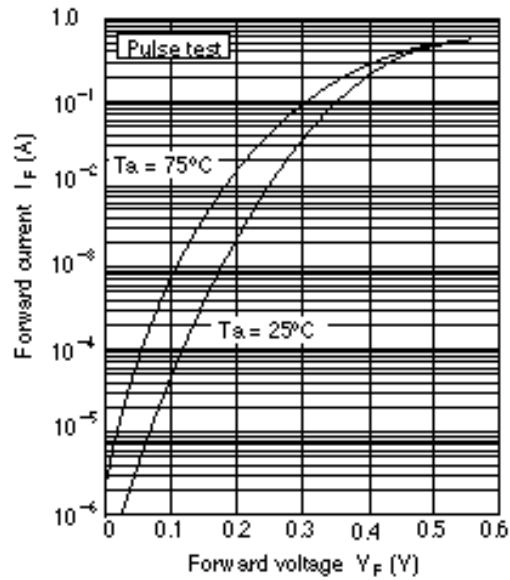


Fig.1 Forward current Vs. Forward voltage

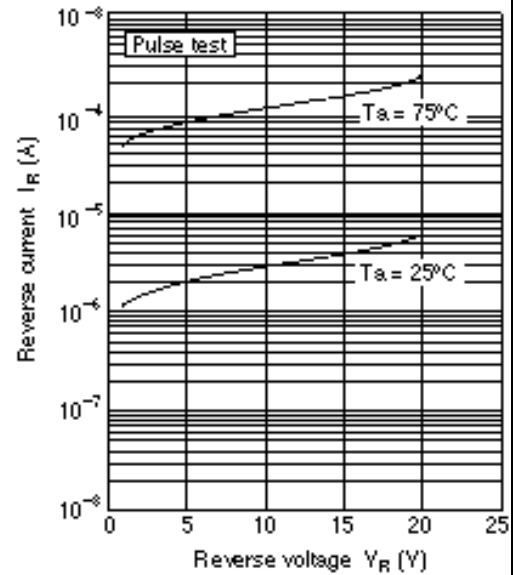


Fig.2 Reverse current Vs. Reverse voltage

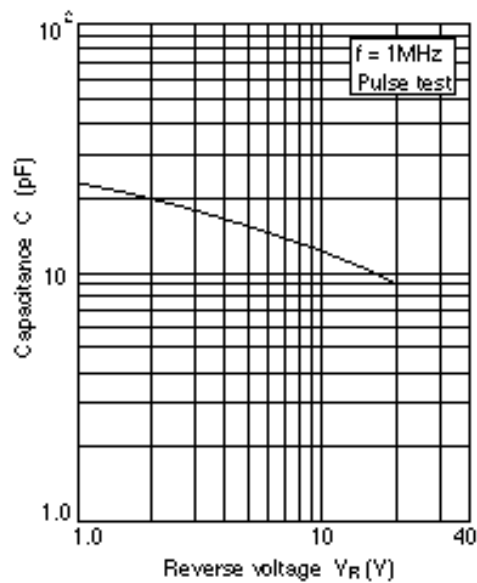


Fig.3 Capacitance Vs. Reverse voltage

Main Characteristic

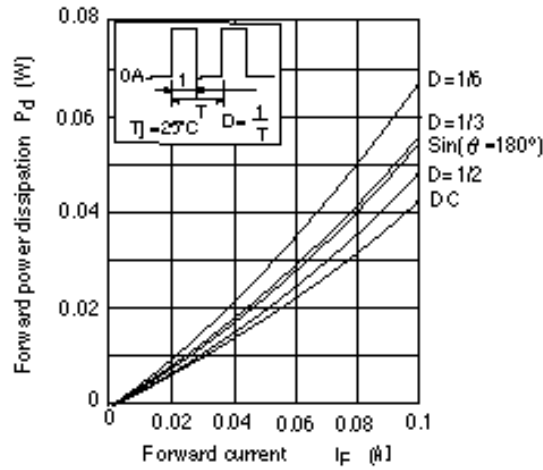


Fig4. Forward power dissipation P_d vs. Forward current I_F

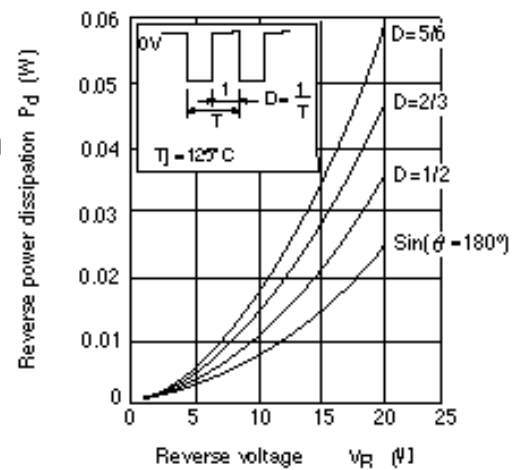


Fig5. Reverse power dissipation P_d vs. Reverse voltage V_R

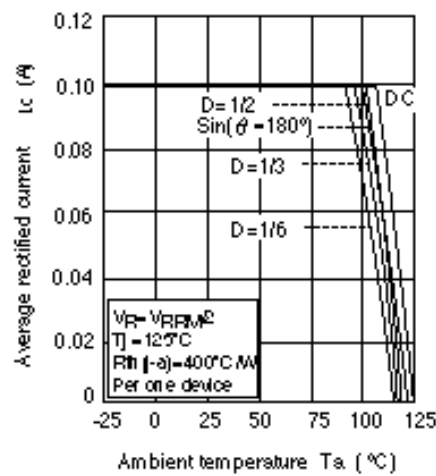


Fig6. Average rectified current I_c vs. Ambient temperature T_a

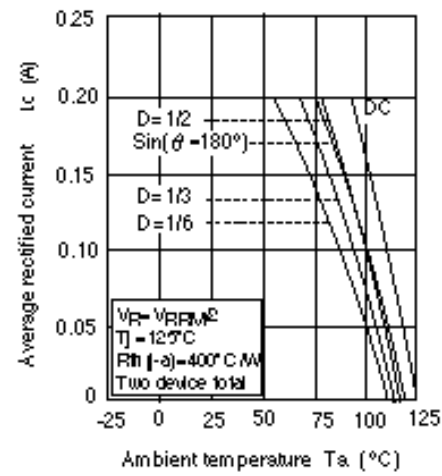


Fig7. Average rectified current I_c vs. Ambient temperature T_a

Package Dimensions

Unit : mm

